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Name of Depositor: Daryl K. Neff

Signature

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of: <b>Michael C. Gaidis et al.</b>	Date: <b>October 24, 2005</b>
Serial Number: <b>10/709,999</b>	Examiner: <b>Dung A. Le</b>
Filed: <b>June 11, 2004</b>	Group Art Unit: <b>2818</b>
Title: <b>STRUCTURE AND METHOD OF PATTERNING A MAGNETIC TUNNEL JUNCTION STACK FOR A MAGNETO-RESISTIVE RANDOM ACCESS MEMORY</b>	Joseph P. Abate IBM Corporation Dept. 18G, Bldg. 321, Zip 482 2070 Route 52 Hopewell Junction, NY 12533

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

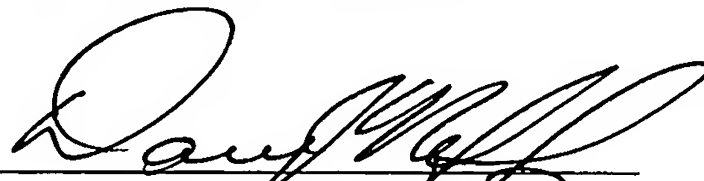
It is respectfully requested that the references listed on the enclosed form be made of record and considered with respect to the above-referenced U.S. patent application. In accordance with the notice at 1276 O.G. 55, copies of U.S. patents and published applications are not enclosed herewith. Submission of the present Information Disclosure Statement should not be taken as an admission that the cited references are legally available prior art or that the same are pertinent or material.

In the event that any fee is due in connection with the present Information Disclosure Statement, the Commissioner is hereby authorized to charge the same to the Deposit Account No. 09-0458 of the Assignee International Business Machines Corporation.

Respectfully submitted,

**Michael C. Gaidis et al.**

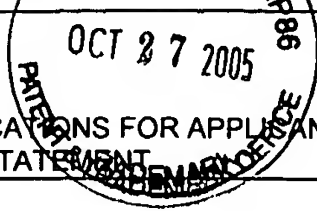
By

A handwritten signature in black ink, appearing to read 'Daryl K. Neff', written over a horizontal line.

Daryl K. Neff, Attorney

Registration No. 38,258

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FORM PTO-1449 (Modified)		ATTY. DOCKET NO. <b>FIS920040017US1</b>	SERIAL NO. <b>10/709,999</b>
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT: <b>Abraham et al.</b>	
(Use several sheets if necessary)		FILING DATE: <b>June 11, 2004</b>	GROUP: <b>2818</b>

## REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NUMBER	ISSUED DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
	AA	5,792,569	08/11/1998	Sun et al.			
	AB	5,946,228	08/31/1999	Abraham et. al.			
	AC	6,034,887	03/07/2000	Gupta et al.			
	AD	6,072,718	06/06/2000	Abraham et al.			
	AE	6,104,633	08/15/2000	Abraham et al.			
	AF	6,299,991 B1	10/09/2001	Bojarczuk, Jr. et al.			
	AG	6,333,067 B2	12/25/2001	Bojarczuk, Jr. et al.			
	AH	6,385,082 B1	05/07/2002	Abraham et al.			
	AI	6,452,764 B1	09/17/2002	Abraham et. al.			
	AJ	6,538,919 B1	03/25/2003	Abraham et al.			
	AK	6,660,568 B1	12/09/2003	Gaidis			
	AL	6,784,091 B1	08/31/2004	Nuetzel et al.			
	AM	6,812,141 B1	11/02/2004	Gaidis et al.			
	AN	2003/0198113 A1	10/23/2003	Abraham et al.			
	AO	2004/0001350 A1	01/01/2004	Abraham et al.			
	AP	2004/0051522 A1	03/18/2004	Worledge et al			
	AQ	2004/0252559 A1	12/16/2004	Gupta			
	AR	2004/0253437 A1	12/16/2004	Ingvarsson et al.			
	AS	2005/0050399 A1	03/03/2005	Abraham et al.			
	AT	2005/0079647 A1	04/14/2005	Abraham et al.			
	AU	2005/0079683 A1	04/14/2005	Sarma et al.			
	AV	2005/0087519 A1	04/28/2005	Klostermann et al.			
	AW	2005/0088875 A1	04/28/2005	Abraham et al.			
	AX	2005/0102581 A1	05/12/2005	Abraham et al.			
	AY	2005/0127418 A1	06/16/2005	Abraham			
	AZ	2005/0151552 A1	07/14/2005	Abraham et al.			
	BA	2005/0185458 A1	08/25/2005	Abraham			

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FILING DATE:

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GROUP:

2818

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

## OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

	CA	Abraham et al., "A 0.18um Logic-Based MRAM Technology for High Performance Nonvolatile Memory Applications," VLSI Conference, IEEE Journal of Solid State Circuits Society, 2003.
	CB	Chen et al. "Magnetic Tunnel Junction Pattern Technique", Journal of Applied Physics, Vol. 93, no. 10, 2003
	CC	DeBrosse et al. "A High-Speed 128Kbit MRAM Core For Future Universal Memory Applications," VLSI Conference, IEEE Journal of Solid State Circuits Society, 2003.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.